



## Si1403CDL vs. Si1403BDL

**Description:** P-Channel, 20 V (D-S) MOSFET

**Package:** SC70-6

**Pin Out:** Identical

**Part Number Replacements:** Si1403CDL-T1-GE3 replaces Si1403BDL-T1-E3  
Si1403CDL-T1-GE3 replaces Si1403BDL-T1-GE3

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)					
PARAMETER	SYMBOL	Si1403CDL	Si1403BDL	UNIT	
Drain-Source Voltage	$V_{DS}$	- 20	- 20	V	
Gate-Source Voltage	$V_{GS}$	$\pm 12$	$\pm 12$		
Continuous Drain Current	$I_D$	$T_A = 25\text{ }^\circ\text{C}$	- 1.6	- 1.5	A
		$T_A = 70\text{ }^\circ\text{C}$	- 1.3	- 1.2 <sup>a</sup>	
Pulsed Drain Current	$I_{DM}$	- 5	- 5		
Continuous Source Current (MOSFET Diode Conduction)	$I_S$	- 0.5	- 0.8		
Power Dissipation	$P_D$	$T_A = 25\text{ }^\circ\text{C}$	0.6	0.625	W
		$T_A = 70\text{ }^\circ\text{C}$	0.4	0.4 <sup>a</sup>	
Operating Junction and Storage Temperature Range	$T_J$ and $T_{stg}$	- 55 to 150	- 55 to 150	$^\circ\text{C}$	
Maximum Junction-to-Ambient	$R_{thJA}$	220	200	$^\circ\text{C/W}$	

SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)								
PARAMETER	SYMBOL	Si1403CDL			Si1403BDL			UNIT
		MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
<b>Static</b>								
Gate-Threshold Voltage	$V_{GS(th)}$	- 0.6		- 1.5	- 0.6		- 1.3	V
Gate-Body Leakage	$I_{GSS}$			$\pm 100$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$			- 1			- 1	$\mu\text{A}$
On-State Drain Current	$V_{GS} = - 4.5\text{ V}$ $I_{D(on)}$	- 2			- 2			A
Drain-Source On-Resistance	$V_{GS} = - 4.5\text{ V}$ $R_{DS(on)}$		0.116	0.140		0.120	0.150	$\Omega$
	$V_{GS} = - 3.6\text{ V}$		0.133	0.160		0.140	0.175	
	$V_{GS} = - 2.5\text{ V}$		0.177	0.222		0.220	0.265	
Forward Transconductance	$g_{fs}$		5			3.4		S
Diode Forward Voltage	$V_{SD}$		- 0.83	- 1.2		- 0.8	- 1.1	V
<b>Dynamic</b>								
Total Gate Charge	$Q_g$		4	8		2.9	4.5	nC
Gate-Source Charge	$Q_{gs}$		0.7			0.65		
Gate-Drain Charge	$Q_{gd}$		1.4			1		
Gate Resistance	$R_g$	2	7	14		9		

**Note**

a.  $T_A = 85\text{ }^\circ\text{C}$  instead of  $70\text{ }^\circ\text{C}$ .

Specification comparisons are supplied as a courtesy to compare two devices and do not constitute a commercial product datasheet or any guarantee of identical performance. Designers should refer to the appropriate datasheets of the same number for guaranteed specification limits.

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